

PSMN4R8-100BSE

N-channel 100 V 4.8 mΩ standard level MOSFET in D2PAK

4 October 2012

Objective data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Enhanced forward Biased safe operating area for superior linear mode operation
- Very low R_{DSon} for low conduction losses

1.3 Applications

- Electronic fuse
- Hot swap
- Load switch
- Soft start

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; Fig. 1	[1]	-	-	120	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	-	405	W
T _j	junction temperature			-55	-	175	°C
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 12 ; Fig. 13		-	-	8.7	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 13		-	4.1	4.8	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V; Fig. 14 ; Fig. 15		-	59	83	nC
Q _{G(tot)}	total gate charge			-	196	278	nC

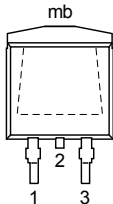
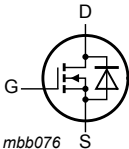


Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche Ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 120\text{ A}$; $V_{\text{sup}} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped; Fig. 3	-	-	542	mJ

[1] Continuous current limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>D2PAK (SOT404)</p>	 <p><i>mbb076</i></p>
2	D	drain ^[1]		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN4R8-100BSE	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R8-100BSE	PSMN4R8-100BSE

5. Limiting values

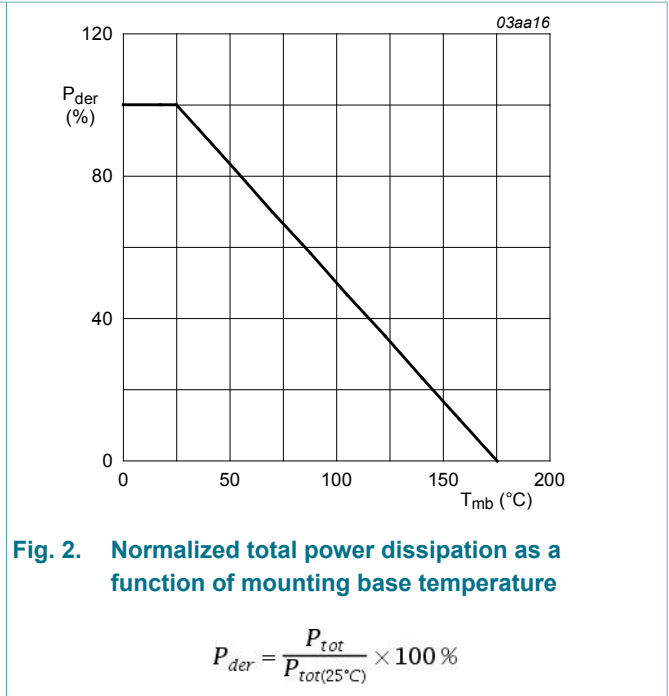
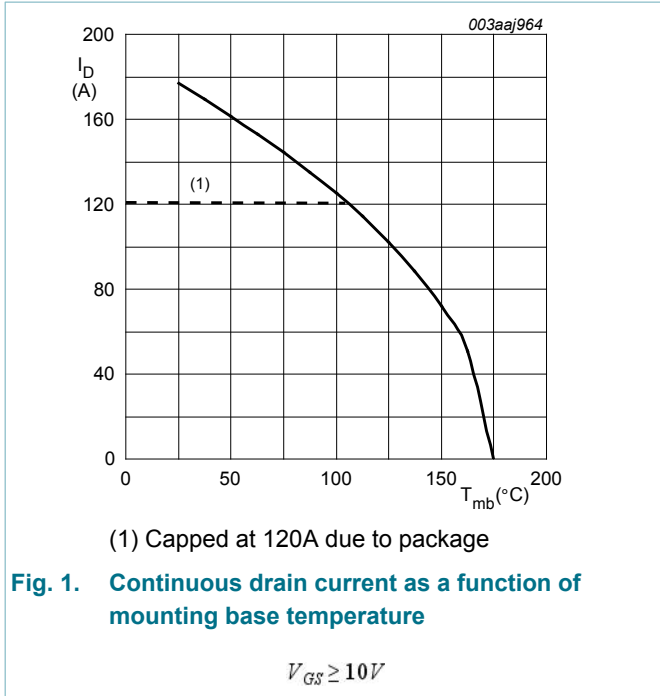
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	100	V

Symbol	Parameter	Conditions		Min	Max	Unit
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _j = 100 °C; Fig. 1	[1]	-	120	A
		V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 1	[1]	-	120	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; Fig. 4		-	707	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	405	W
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{slid(M)}	peak soldering temperature			-	260	°C
Source-drain diode						
I _S	source current	T _{mb} = 25 °C	[1]	-	120	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	707	A
Avalanche Ruggedness						
E _{D(S(AL)S)}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 120 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; unclamped; Fig. 3		-	542	mJ

[1] Continuous current limited by package.



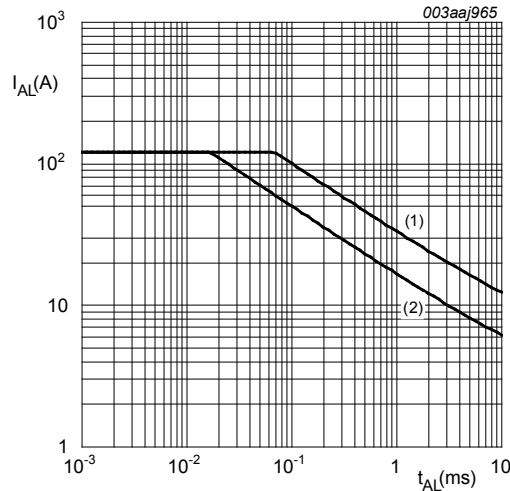


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (int)} = 25^{\circ}C$; (2) $T_{j (int)} = 100^{\circ}C$

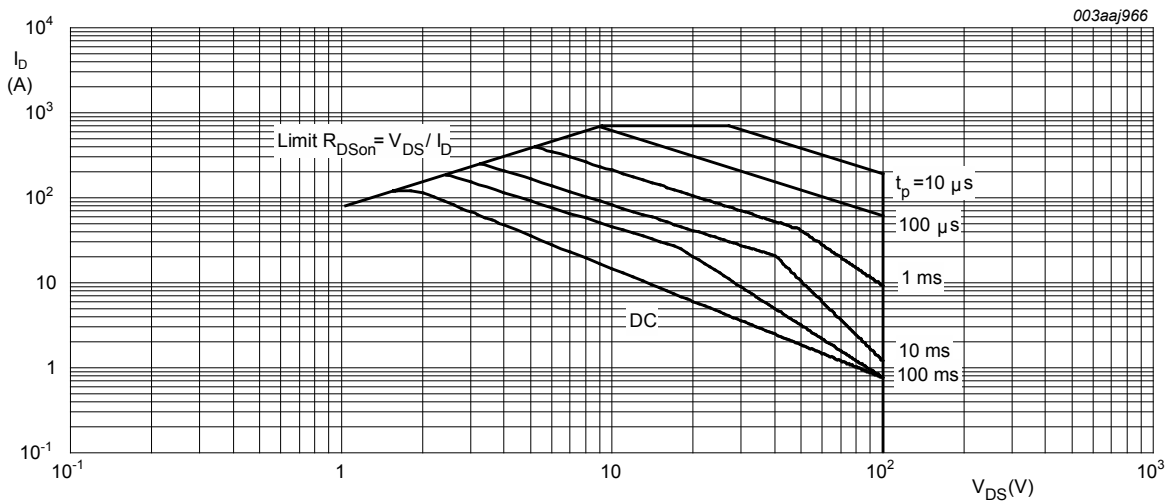


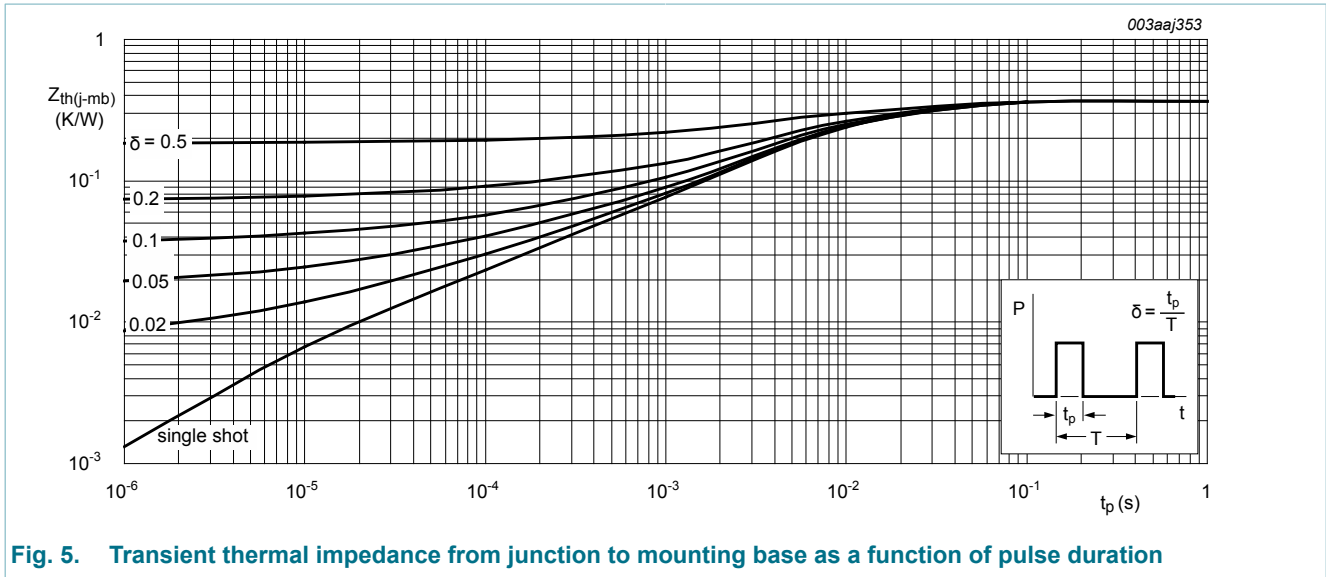
Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse; Capped at 120 A due to package

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.3	0.37	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$; Fig. 10 ; Fig. 11	2	3	4	V
V_{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$; Fig. 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$; Fig. 11	-	-	4.6	V
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.16	10	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	10	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ C$; Fig. 12 ; Fig. 13	-	-	8.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C$; Fig. 12 ; Fig. 13	-	-	13	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C$; Fig. 13	-	4.1	4.8	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$	0.43	0.85	1.7	Ω

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25\text{ A}; V_{DS} = 50\text{ V}; V_{GS} = 10\text{ V};$ Fig. 14 ; Fig. 15	-	196	278	nC
Q_{GS}	gate-source charge		-	40	56	nC
Q_{GD}	gate-drain charge		-	59	83	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\text{ A}; V_{DS} = 50\text{ V};$ Fig. 14 ; Fig. 15	-	4.3	-	V
C_{iss}	input capacitance	$V_{DS} = 50\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 16	-	10665	14400	pF
C_{oss}	output capacitance		-	674	910	pF
C_{rss}	reverse transfer capacitance		-	459	643	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50\text{ V}; R_L = 2\text{ } \Omega; V_{GS} = 10\text{ V};$ $R_{G(ext)} = 4.7\text{ } \Omega$	-	41	61.5	ns
t_r	rise time		-	65	97.5	ns
$t_{d(off)}$	turn-off delay time		-	127	190.5	ns
t_f	fall time		-	69	103.5	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 17	-	0.79	1.2	V
t_{rr}	reverse recovery time	$I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 50\text{ V}$	-	72	94	ns
Q_r	recovered charge		-	227	296	nC

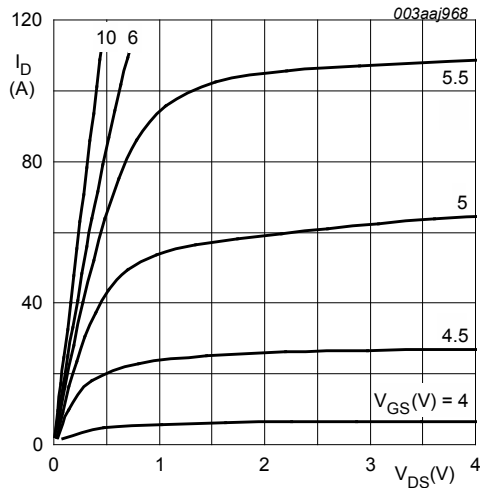


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

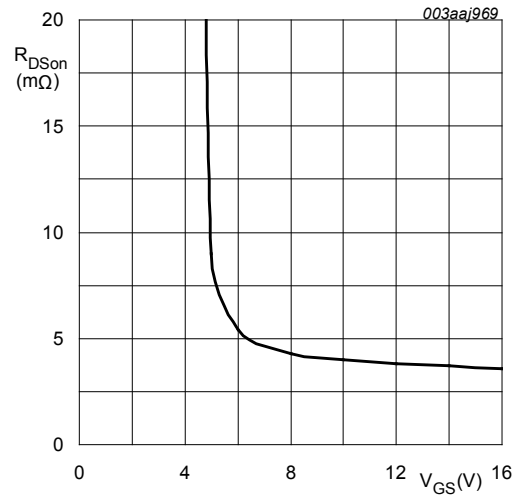


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

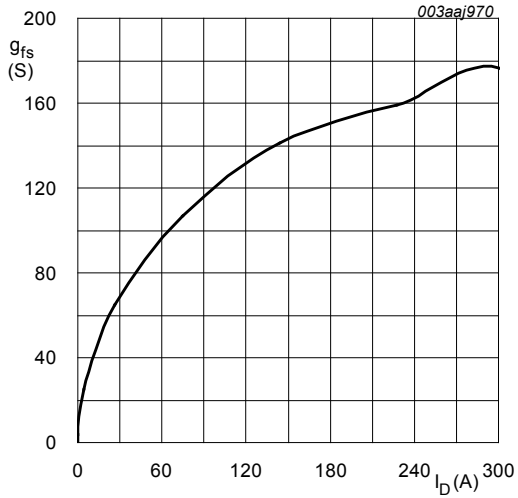


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$

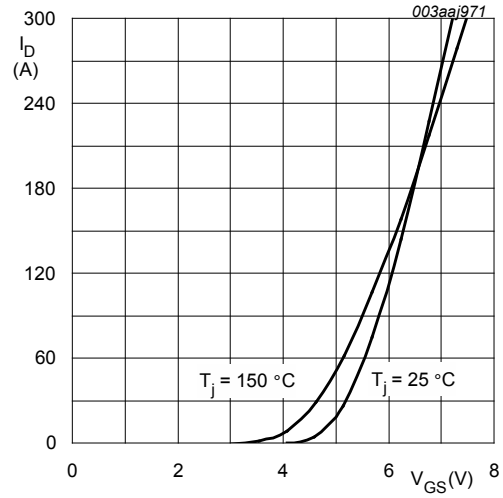


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{V}$

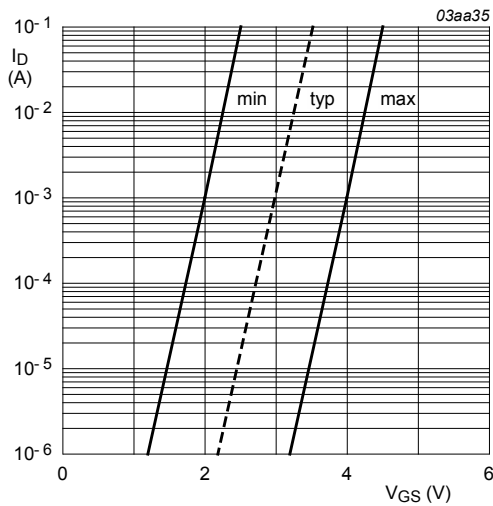


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

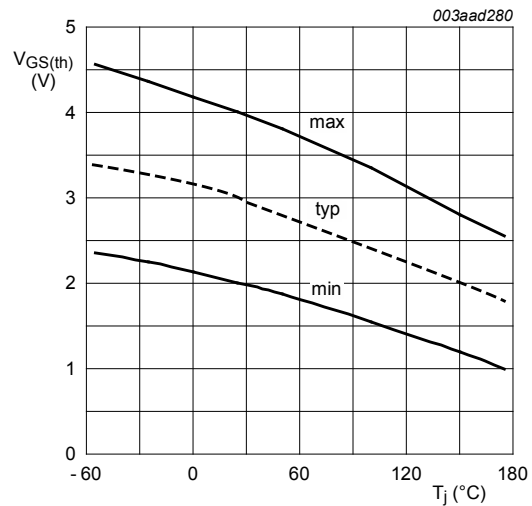


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

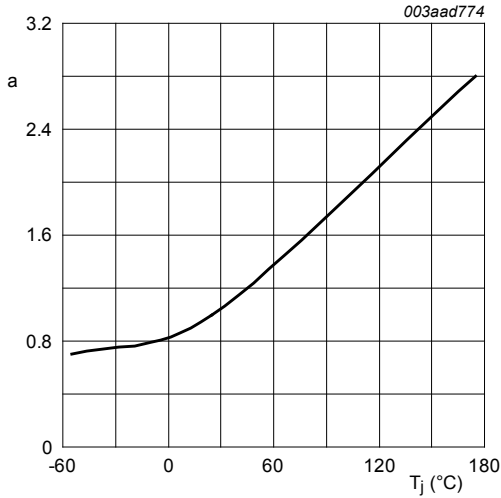


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

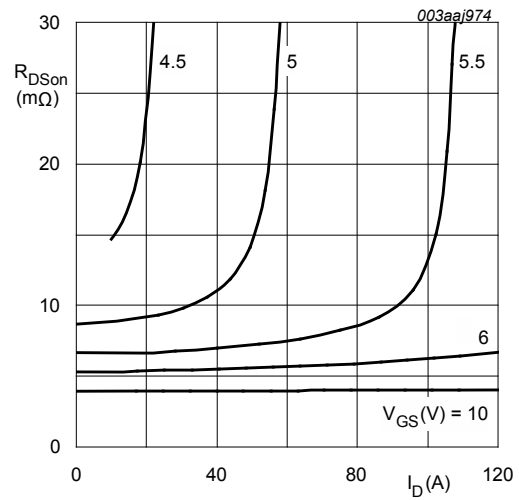


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^\circ C$

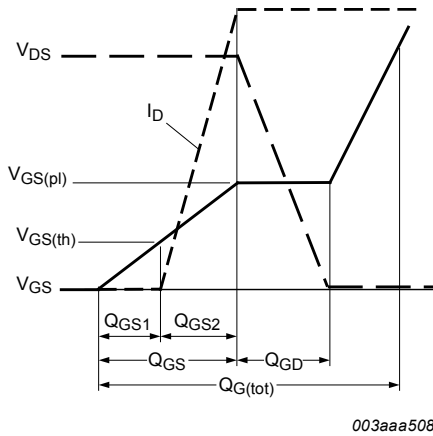


Fig. 14. Gate charge waveform definitions

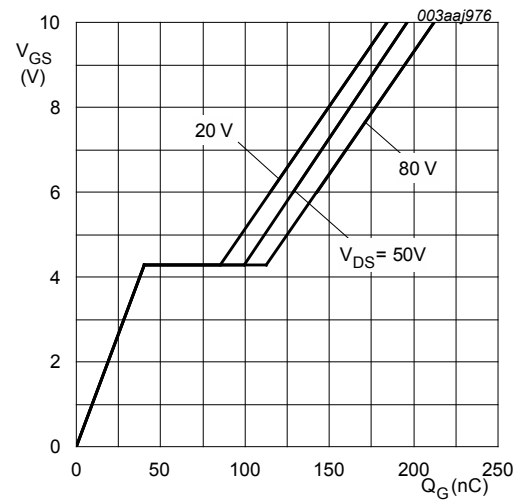


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ C; I_D = 25A$

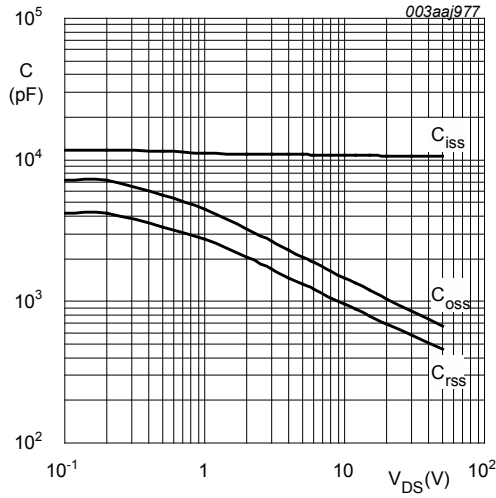


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

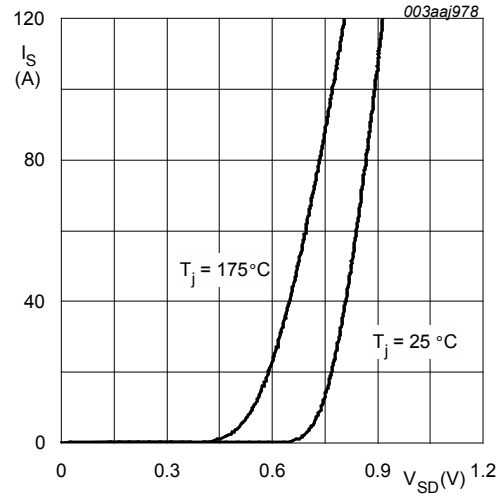


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

8. Package outline

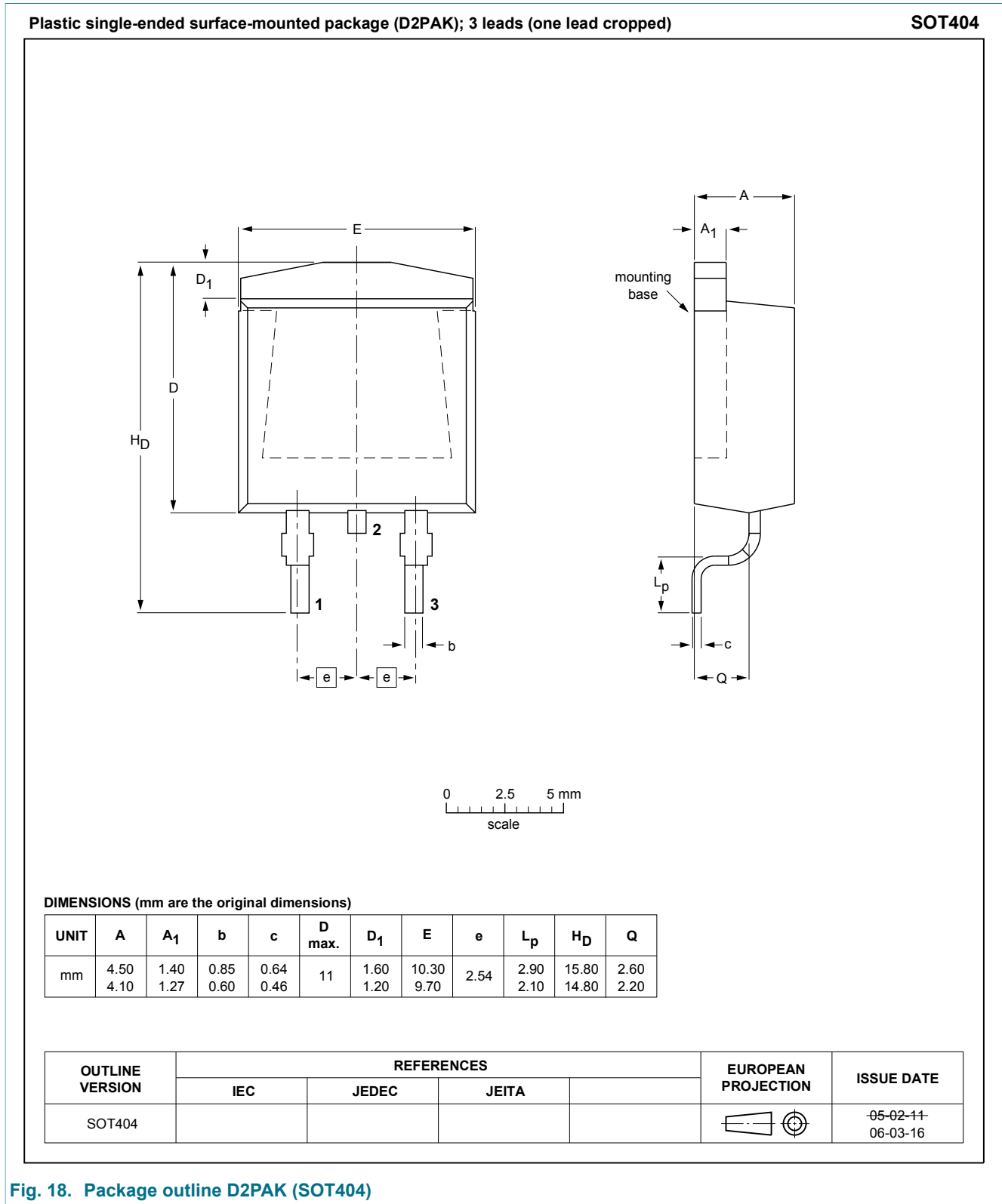


Fig. 18. Package outline D2PAK (SOT404)

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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